

## 1. General description

Silicon Carbide MOSFET in a TO263-7L plastic package, designed for high frequency, high efficiency systems.



AEC - Q101 Qualified



## 2. Features and benefits

- Kelvin source configuration
- Low on-resistance
- Fast switching speed
- 0V turn-off  $V_{GS}$  for simple gate driving
- 100% UIS Tested
- Easy to parallel
- RoHS compliant

## 3. Applications

- Automotive on board chargers
- Automotive DC-DC converters
- Automotive electric compressor motor drives
- HV battery management systems

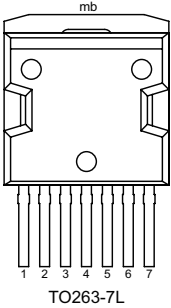
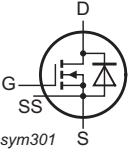
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		1200			V
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ °C}$		93			A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}, T_j = 175\text{ °C}$		417			W
$T_j$	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15\text{ V}; I_D = 40\text{ A}; T_j = 25\text{ °C}$		-	30	-	mΩ
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 40\text{ A}; V_{DS} = 800\text{ V}; V_{GS} = -4\text{ V}/18\text{ V}; T_j = 25\text{ °C}$		-	151	-	nC
$Q_{GD}$	gate-drain charge			-	21	-	nC
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_{SD} = 40\text{ A}; di/dt = 500\text{ A}/\mu\text{s}; V_{DS} = 400\text{ V}; T_j = 25\text{ °C}$		-	129	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO263-7L</p>	 <p>sym301</p>
2	SS	source sense		
3-7	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2M30120B7-A	TO263-7L	WNSC2M30120B7-A6J	Reel	800	TO263P-7L	12-Jun-2023

## 7. Marking

Table 4. Marking codes

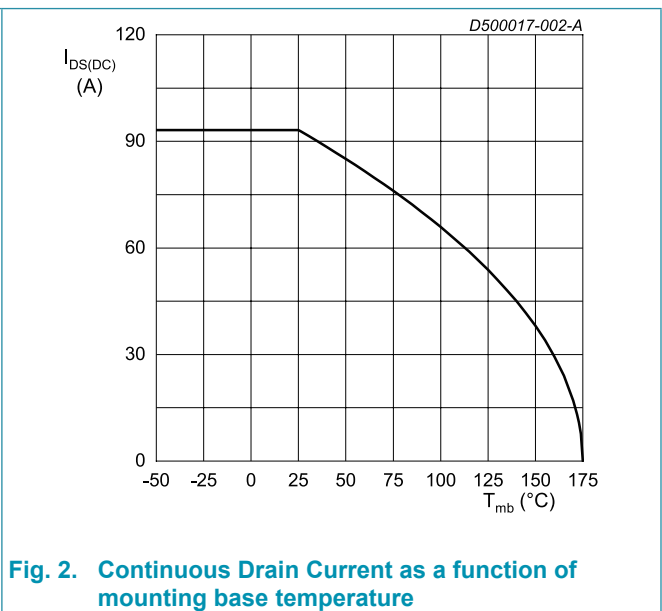
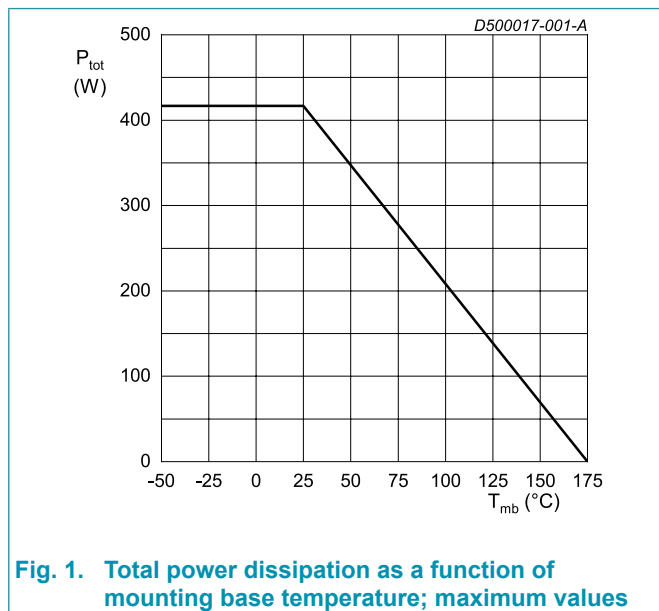
Type number	Marking codes
WNSC2M30120B7-A	WNSC2M 30120B7-A

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		1200	V
$V_{GS,max}$	gate-source voltage			-10 to 22	V
$V_{GS,op}$	gate-source voltage			-4 to 18	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}, T_j = 175\text{ °C}$		417	W
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ °C}$		93	A
		$V_{GS} = 18\text{ V}; T_{mb} = 100\text{ °C}$		65	A
$I_{DM}$	peak drain current	pulse width $t_p$ limited by $T_{jmax}$	Fig.17	186	A
$I_S$	continuous diode current	$V_{GS} = -4\text{ V}; T_{mb} = 25\text{ °C}$		70	A
$I_{SM}$	pulse diode current	$V_{GS} = -4\text{ V};$ pulse width $t_p$ limited by $T_{jmax}$		186	A
$E_{as}$	single pulse drain-to-source avalanche	$I_{AS} = 20\text{ A}; L = 1\text{ mH}; V_{DD} = 100\text{ V}; T_j = 25\text{ °C}$		200	mJ
$T_{stg}$	storage temperature			-55 to 175	°C
$T_j$	junction temperature			-55 to 175	°C
$T_{sld(M)}$	peak soldering temperature			260	°C

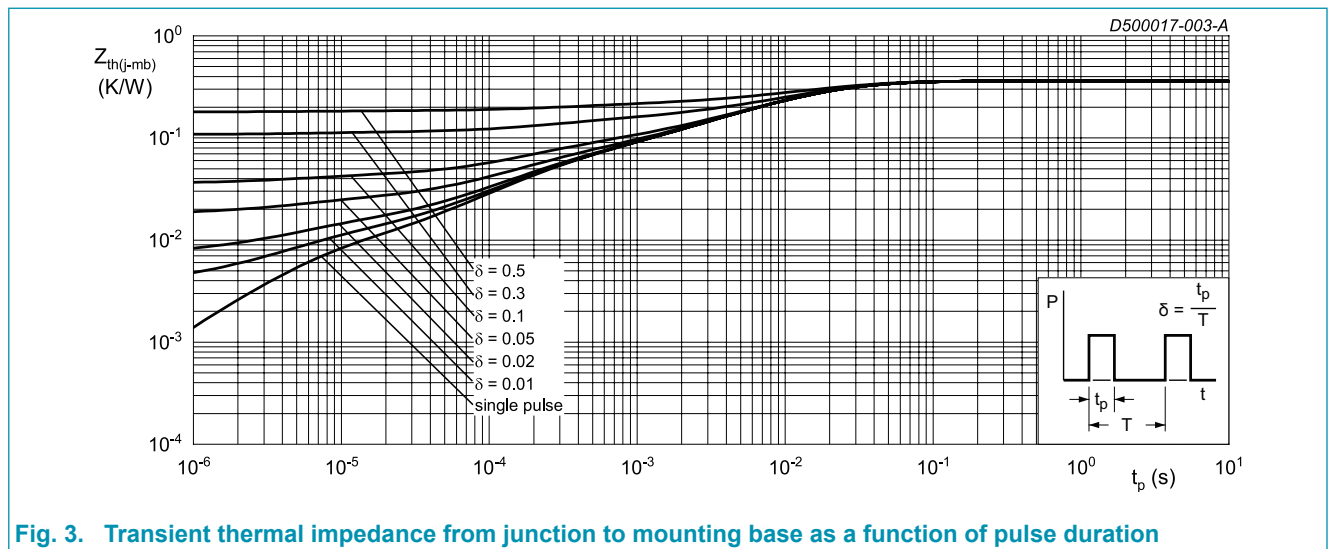


## 9. Thermal & Mechanical characteristics

**Table 6. Thermal & Mechanical characteristics**

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	0.36	-	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	40	-	K/W

Note: It is recommended that a metal washer is inserted between screw head and mounting tab.  
Do not use self-tapping screws.  
Device is ESD sensitive. Handling precautions are recommended.

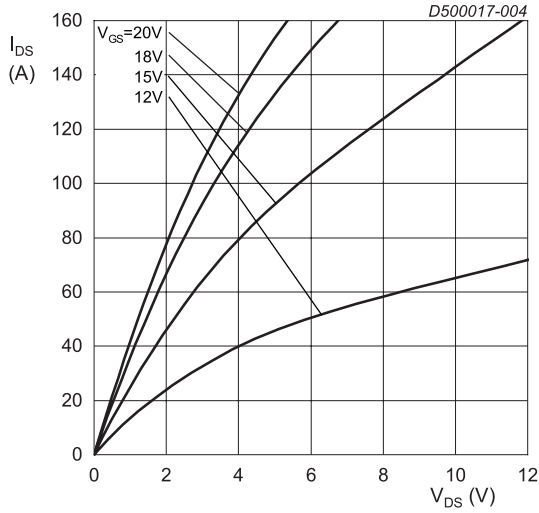


**Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 10. Characteristics

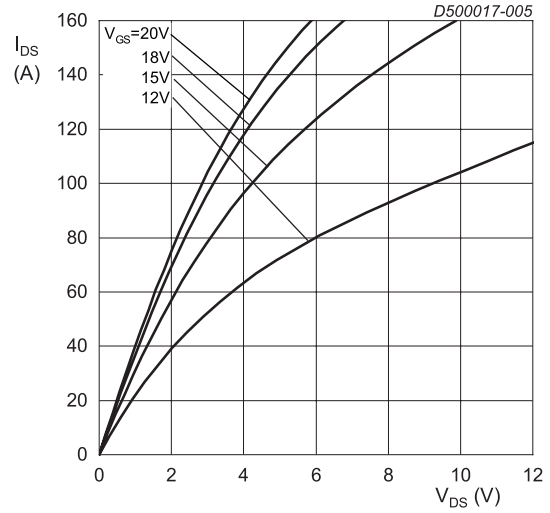
Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 100 \mu A; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$		1200	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 12 \text{ mA}; V_{DS} = 10 \text{ V}; T_J = 25 \text{ }^\circ C$		1.9	2.6	3.5	V
		$I_D = 12 \text{ mA}; V_{DS} = 10 \text{ V}; T_J = 175 \text{ }^\circ C$		-	1.9	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$		-	0.2	100	$\mu A$
		$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 175 \text{ }^\circ C$		-	2	-	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 24 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$		-	10	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$		-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15 \text{ V}; I_D = 40 \text{ A}; T_J = 25 \text{ }^\circ C$		-	30	-	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 40 \text{ A}; T_J = 25 \text{ }^\circ C$		-	24	40	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 40 \text{ A}; T_J = 175 \text{ }^\circ C$		-	48	-	m $\Omega$
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_J = 25 \text{ }^\circ C$		-	0.8	-	$\Omega$
$g_{fs}$	transconductance	$V_{DS} = 20 \text{ V}; I_D = 40 \text{ A}; T_J = 25 \text{ }^\circ C$		-	27	-	S
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 40 \text{ A}; V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; T_J = 25 \text{ }^\circ C$		-	151	-	nC
$Q_{GS}$	gate-source charge			-	63	-	nC
$Q_{GD}$	gate-drain charge			-	21	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 1000 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_J = 25 \text{ }^\circ C$		-	3305	-	pF
$C_{oss}$	output capacitance			-	139	-	pF
$C_{rss}$	reverse transfer capacitance			-	12	-	pF
$E_{oss}$	Coss stored energy			-	70	-	$\mu J$
$t_{d(on)}$	turn-on delay time	$V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; R_{G(ext)} = 3.6 \text{ } \Omega; I_D = 40 \text{ A}; L = 330 \text{ } \mu H; T_J = 25 \text{ }^\circ C$		-	14	-	ns
$t_r$	rise time			-	27	-	ns
$t_{d(off)}$	turn-off delay time			-	43	-	ns
$t_f$	fall time			-	50	-	ns
$E_{on}$	turn-on energy <small>(Body Diode FWD)</small>		Fig.20	-	260	-	$\mu J$
$E_{off}$	turn-off energy <small>(Body Diode FWD)</small>		Fig.20	-	156	-	$\mu J$
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$V_{GS} = 0 \text{ V}; I_{SD} = 20 \text{ A}; T_J = 25 \text{ }^\circ C$		-	3.2	-	V
		$V_{GS} = -4 \text{ V}; I_{SD} = 20 \text{ A}; T_J = 25 \text{ }^\circ C$		-	4.8	-	V
		$V_{GS} = -4 \text{ V}; I_{SD} = 20 \text{ A}; T_J = 175 \text{ }^\circ C$		-	4.2	-	V
$t_{rr}$	reverse recovery time	$I_{SD} = 40 \text{ A}; di/dt = 500 \text{ A}/\mu s; V_{DS} = 400 \text{ V}; T_J = 25 \text{ }^\circ C$		-	33	-	ns
$Q_r$	recovered charge			-	129	-	nC
$I_{rrm}$	reverse recovery current			-	6.9	-	A



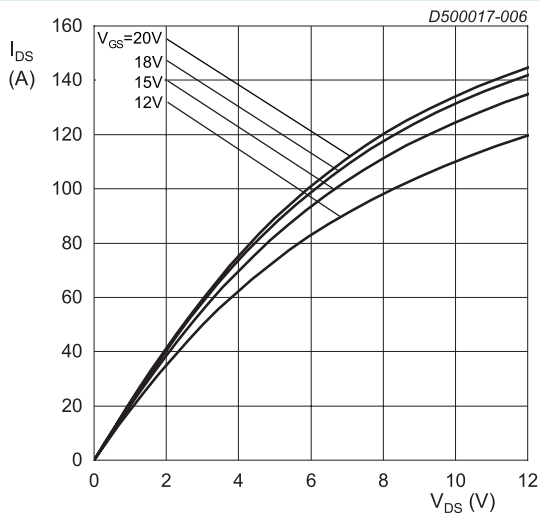
$T_j = -55\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$

**Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values**



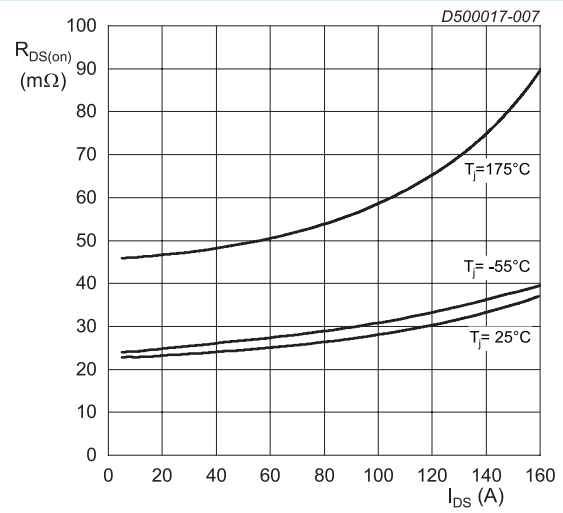
$T_j = 25\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$

**Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values**



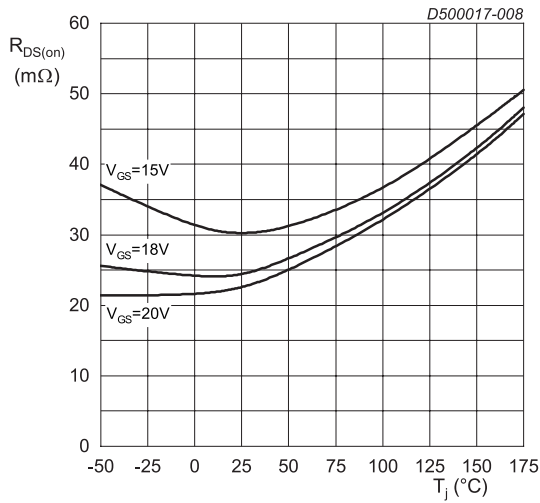
$T_j = 175\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**

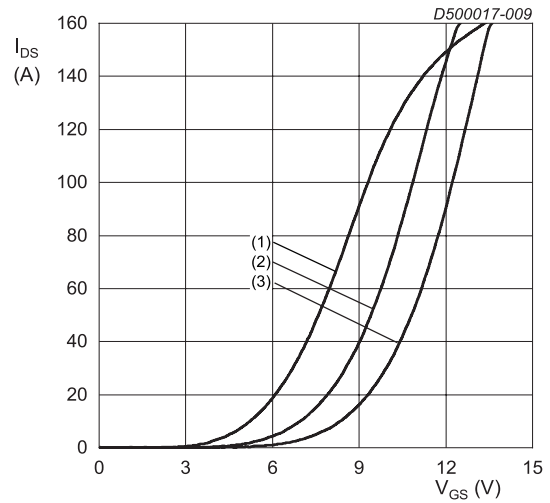


$V_{GS} = 18\text{ V}; t_p < 200\text{ }\mu\text{s}$

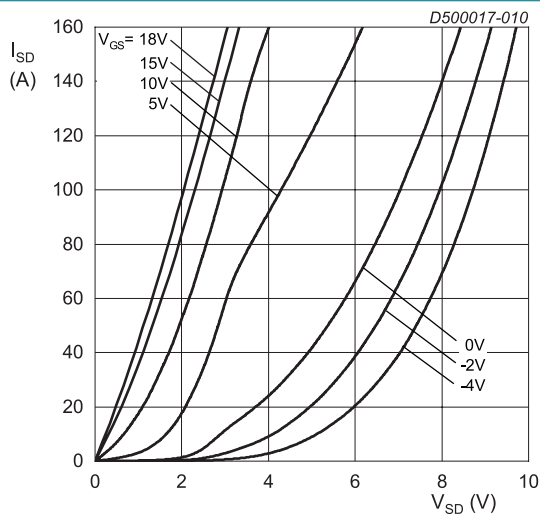
**Fig. 7. Drain-source on-state resistance as a function of drain current; typical values**



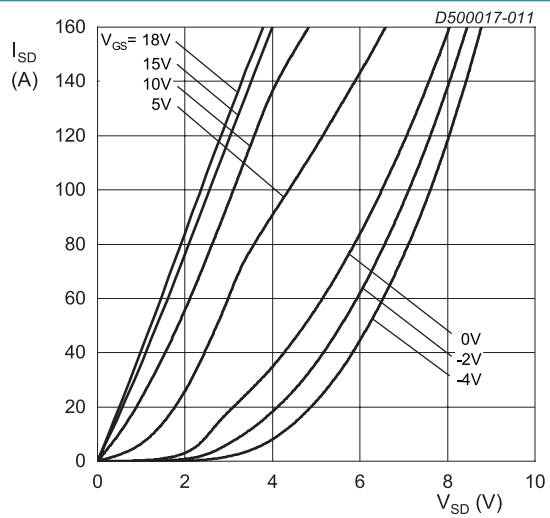
$I_{DS} = 40 A; t_p < 200 \mu s$   
**Fig. 8. Drain-source on-state resistance as a function of junction temperature**



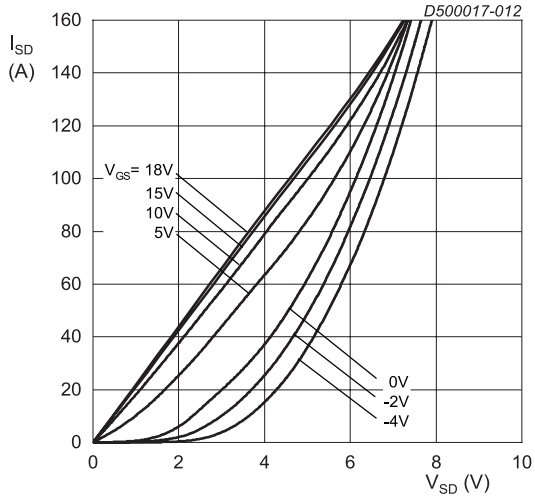
$V_{DS} = 20 V; t_p < 200 \mu s$   
 (1)  $T_j = 175 ^{\circ}$ C  
 (2)  $T_j = 25 ^{\circ}$ C  
 (3)  $T_j = -55 ^{\circ}$ C  
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



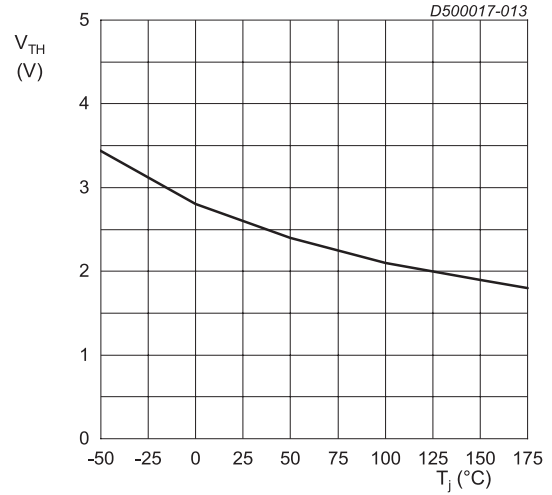
$T_j = -55 ^{\circ}$ C;  $t_p < 200 \mu s$   
**Fig. 10. Body diode forward characteristics; typical values**



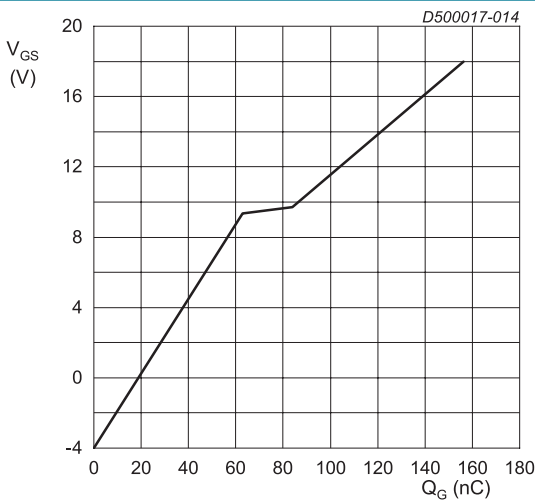
$T_j = 25 ^{\circ}$ C;  $t_p < 200 \mu s$   
**Fig. 11. Body diode forward characteristics; typical values**



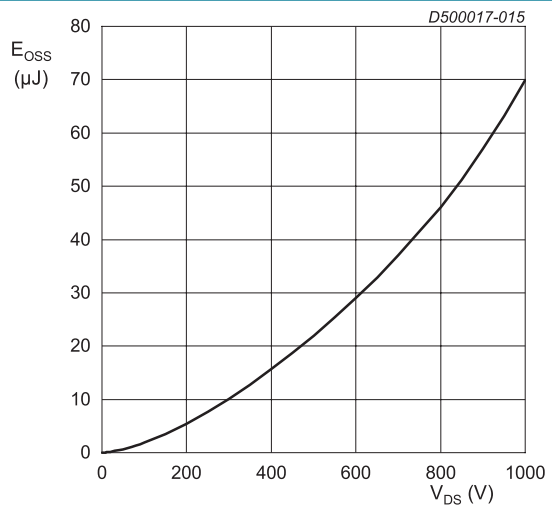
$T_j = 175\text{ }^\circ\text{C}$ ;  $t_p < 200\text{ }\mu\text{s}$   
**Fig. 12. Body diode forward characteristics; typical values**



$V_{DS} = 10\text{ V}$ ;  $I_{DS} = 12\text{ mA}$   
**Fig. 13. Threshold voltage as a function of junction temperature**

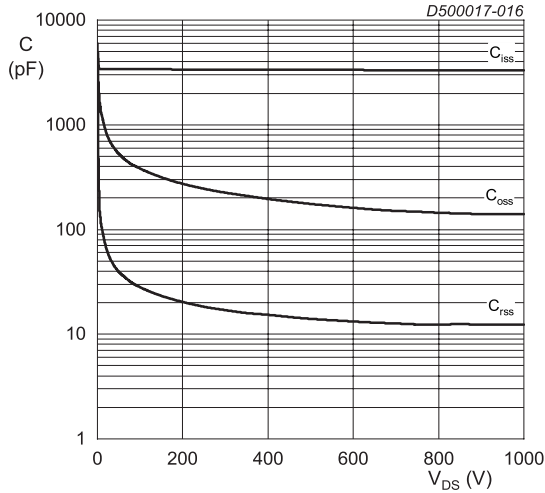


$I_{DS} = 40\text{ A}$ ;  $I_{GS} = 0.1\text{ mA}$ ;  $V_{DS} = 800\text{ V}$ ;  $T_j = 25\text{ }^\circ\text{C}$   
**Fig. 14. Gate-source voltage as a function of gate charge; typical values**



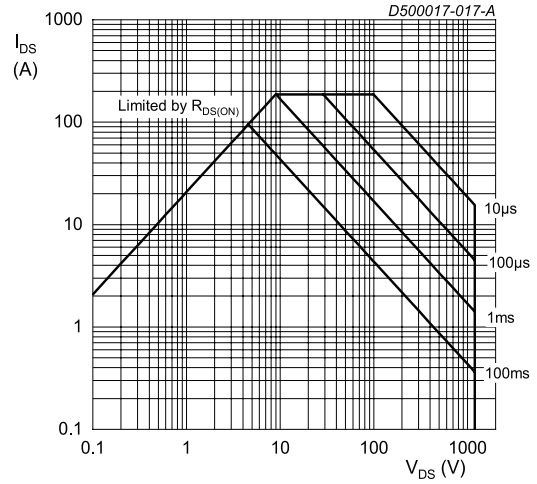
**Fig. 15. Output capacitor stored energy as a function of drain-source voltage**





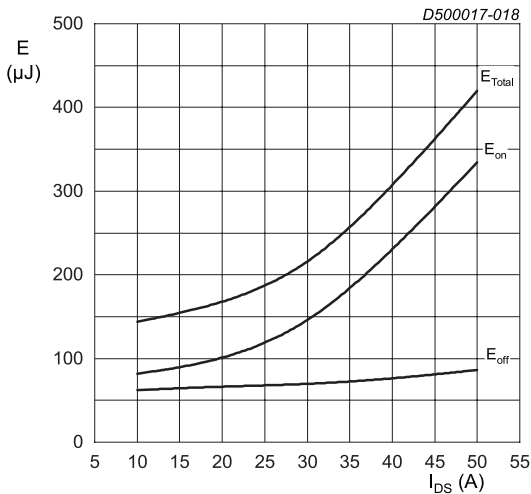
$V_{DS} = 0 - 1000 \text{ V}$   
 $T_j = 25 \text{ }^\circ\text{C}; V_{AC} = 25 \text{ mV}; f = 1 \text{ MHz}$

**Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



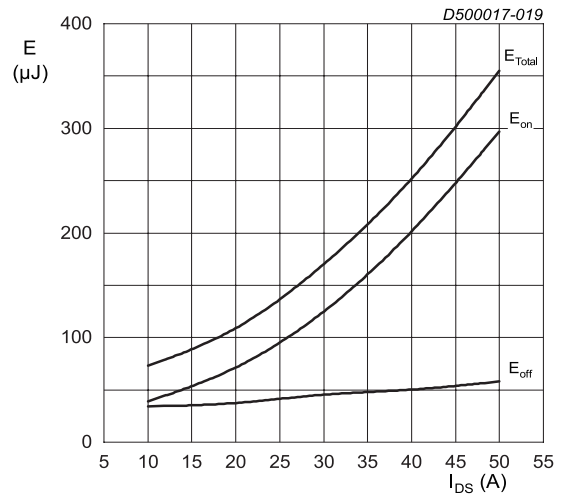
$T_j = 25 \text{ }^\circ\text{C}; D = 0$   
 Parameter:  $t_p$

**Fig. 17. Forward bias safe operating area**



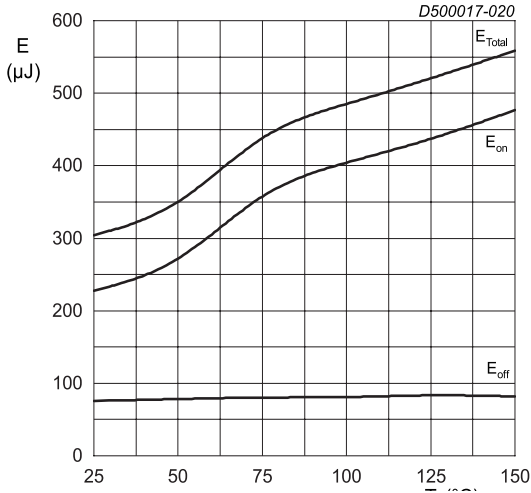
$T_j = 25 \text{ }^\circ\text{C}; V_{DD} = 800 \text{ V}; R_{G(ext)} = 3.6 \text{ } \Omega;$   
 $V_{GS} = -4 \text{ V}/18 \text{ V}; L = 330 \text{ } \mu\text{H}$   
 FWD = WNSC2M30120B7-A

**Fig. 18. Clamped Inductive Switching Energy as a function of drain current**



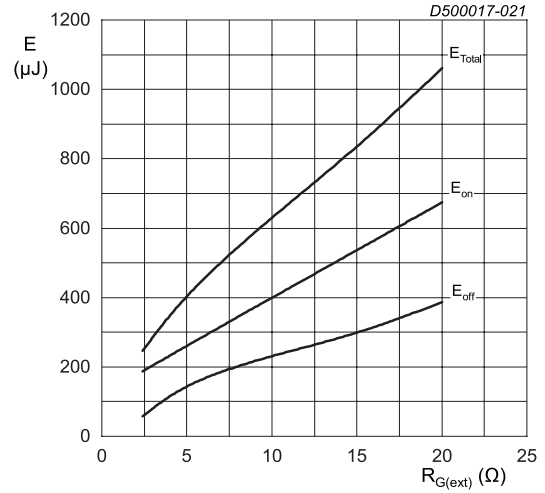
$T_j = 25 \text{ }^\circ\text{C}; V_{DD} = 600 \text{ V}; R_{G(ext)} = 3.6 \text{ } \Omega;$   
 $V_{GS} = -4 \text{ V}/18 \text{ V}; L = 330 \text{ } \mu\text{H}$   
 FWD = WNSC2M30120B7-A

**Fig. 19. Clamped Inductive Switching Energy as a function of drain current**



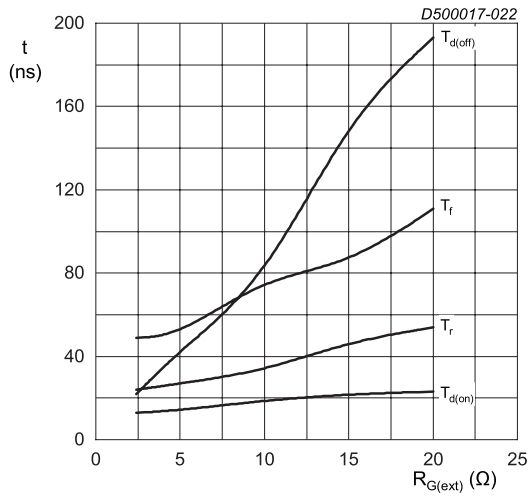
$I_{DS} = 40 \text{ A}; V_{DD} = 800 \text{ V}; R_{G(ext)} = 3.6 \text{ } \Omega;$   
 $V_{GS} = -4 \text{ V}/18 \text{ V}; L = 330 \text{ } \mu\text{H}$   
 FWD = WNSC2M30120B7-A

**Fig. 20. Clamped Inductive Switching Energy as a function of junction temperature**



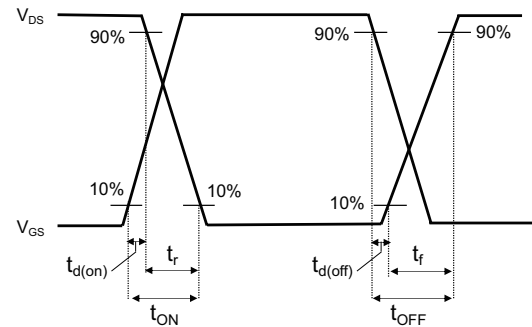
$T_j = 25 \text{ } ^\circ\text{C}; V_{DD} = 800 \text{ V}; I_{DS} = 40 \text{ A}; V_{GS} = -4 \text{ V}/18 \text{ V}$   
 FWD = WNSC2M30120B7-A;  $L = 330 \text{ } \mu\text{H}$

**Fig. 21. Clamped Inductive Switching Energy as a function of external gate resistance**



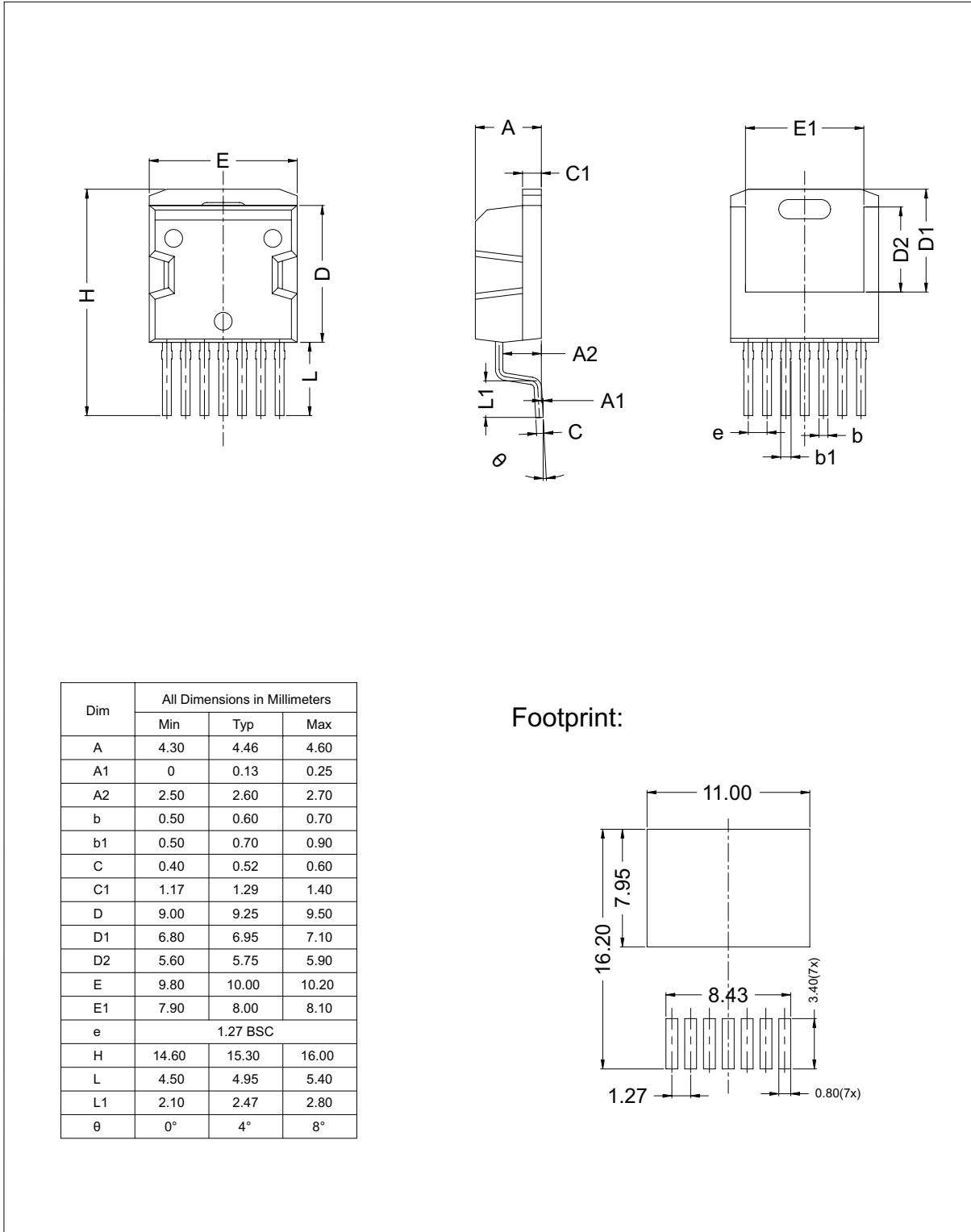
$T_j = 25 \text{ } ^\circ\text{C}; V_{DD} = 800 \text{ V}; I_{DS} = 40 \text{ A}; V_{GS} = -4 \text{ V}/18 \text{ V}$   
 FWD = WNSC2M30120B7-A;  $L = 330 \text{ } \mu\text{H}$

**Fig. 22. Switching time as a function of external gate resistance**



**Fig. 23. Switching time definition**

### 11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: <http://www.ween-semi.com>  
For sales office addresses, please send an email to: [salesaddresses@ween-semi.com](mailto:salesaddresses@ween-semi.com)  
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